Product data sheet

1. General description

PNP low VCEsat single bipolar PNP transistor in a SOT457 (SC-74) SMD plastic package.

NPN complement: PBSS4440D

2. Features and benefits

- Ultra low collector-emitter saturation voltage VCEsat
- 4 A continuous collector current capability IC (DC)
- Up to 15 A peak current
- · Very low collector-emitter saturation resistance
- High efficiency due to less heat generation
- AEC-Q101 qualified

3. Applications

- Power management functions
- Charging circuits
- DC-to-DC conversion
- MOSFET gate driving
- · Power switches (e.g. motors, fans)
- Thin Film Transistor (TFT) backlight inverter

4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
V _{CEO}	collector-emitter voltage	open base		-	-	-40	V
I _C	collector current		[1]	-	-	-4	Α
I _{CM}	peak collector current	limited by $T_{j(max)}$; single pulse; $t_p = 1 \text{ ms}$		-	-	-15	Α
R _{CEsat}	collector-emitter saturation resistance	I_C = -6 A; I_B = -600 mA; pulsed; $t_p \le$ 300 µs; $\delta \le$ 0.02; T_{amb} = 25 °C		-	55	75	mΩ

[1] Device mounted on a ceramic PCB, Al₂O₃, standard footprint.



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5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	С	collector		
2	С	collector	<u> </u>	C
3	В	base		В — 🗽
4	E	emitter	<u>0</u> <u>∃1 ∃2 ∃3</u>	, , , , , , , , , , , , , , , , , , ,
5	С	collector	TSOP6 (SOT457)	sym030
6	С	collector		,

6. Ordering information

Table 3. Ordering information

Type number	Package				
	Name	Description	Version		
PBSS5440D	TSOP6	plastic, surface-mounted package (SC-74; TSOP6); 6 leads	SOT457		

7. Marking

Table 4. Marking codes

Type number	Marking code
PBSS5440D	71

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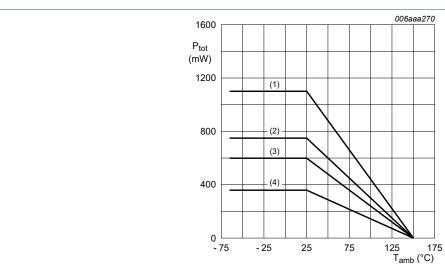
8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V _{CBO}	collector-base voltage	open emitter		-	-40	V
V _{CEO}	collector-emitter voltage	open base		-	-40	V
V _{EBO}	emitter-base voltage	open collector		-	-5	V
Ic	collector current		[1]	-	-4	Α
I _{CM}	peak collector current	limited by $T_{j(max)}$; single pulse; $t_p = 1 \text{ ms}$		-	-15	Α
I _B	base current			-	-0.8	Α
I _{BM}	peak base current	single pulse; t _p ≤ 300 µs		-	-2	Α
P _{tot}	total power dissipation	T _{amb} ≤ 25 °C	[2]	-	360	mW
			[3]	-	600	mW
			[4]	-	750	mW
			[1]	-	1.1	W
			[2] [5]	-	2.5	W
Tj	junction temperature			-	150	°C
T _{amb}	ambient temperature			-65	150	°C
T _{stg}	storage temperature			-65	150	°C

- Device mounted on a ceramic PCB, Al₂O₃, standard footprint.
- Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 1 cm². [3]
- Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 6 cm². [4]
- [5] Operated under pulsed conditions: Duty cycle $\delta \le 10$ % and pulse width $t_p \le 10$ ms.



- (1) Ceramic PCB, Al_2O_3 , standard footprint
- (2) FR4 PCB, mounting pad for collector 6 cm²
- (3) FR4 PCB, mounting pad for collector 1 cm²
- (4) FR4 PCB, standard footprint

Power derating curves Fig. 1.

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9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
R _{th(j-a)}	thermal resistance from	in free air [1] [2] [3] [4] [1] [5]	[1]	-	-	350	K/W
	junction to ambient		[2]	-	-	208	K/W
			[3]	-	-	160	K/W
			-	-	113	K/W	
			[1] [5]	-	-	50	K/W
R _{th(j-sp)}	thermal resistance from junction to solder point			-	-	45	K/W

- [1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- [2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 1 cm²
- [3] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 6 cm².
- [4] Device mounted on a ceramic PCB, Al₂O₃, standard footprint.
- [5] Operated under pulsed conditions: Duty cycle $\delta \le 10$ % and pulse width $t_p \le 10$ ms.

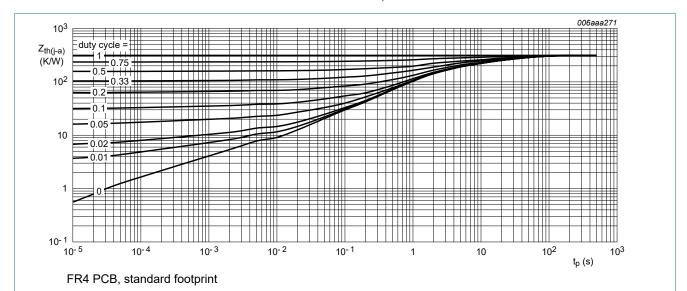


Fig. 2. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

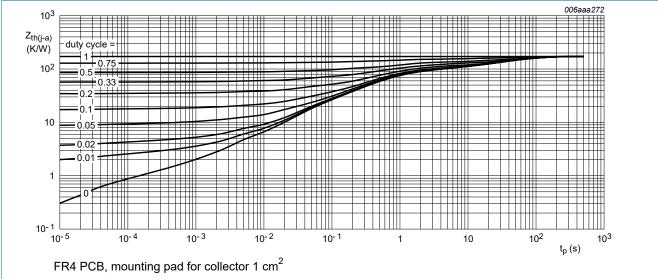
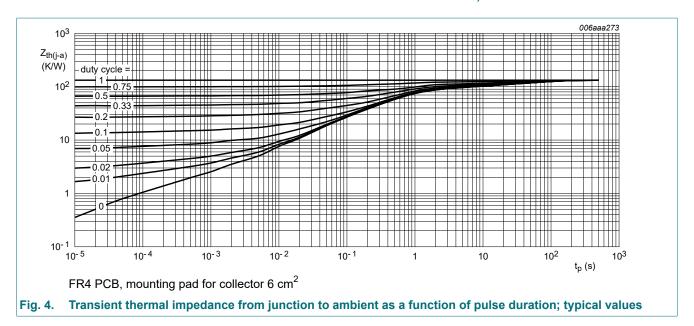


Fig. 3. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

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10. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
СВО	collector-base cut-off	V _{CB} = -30 V; I _E = 0 A; T _{amb} = 25 °C	-	-	-100	nA
	current	V _{CB} = -30 V; I _E = 0 A; T _j = 150 °C	-	-	-50	μA
ЕВО	emitter-base cut-off current	$V_{EB} = -5 \text{ V}; I_C = 0 \text{ A}; T_{amb} = 25 \text{ °C}$	-	-	-100	nA
CES	collector-emitter cut-off current	V _{CE} = -30 V; V _{BE} = 0 V; T _{amb} = 25 °C	-	-	-100	nA
h _{FE}	DC current gain	V _{CE} = -2 V; I _C = -0.5 A; T _{amb} = 25 °C	200	-	-	
		V_{CE} = -2 V; I_{C} = -1 A; pulsed; t_{p} ≤ 300 μs; δ ≤ 0.02; T_{amb} = 25 °C	200	-	-	
		V_{CE} = -2 V; I_{C} = -2 A; pulsed; t_{p} ≤ 300 μs; δ ≤ 0.02; T_{amb} = 25 °C	175	-	-	
		V_{CE} = -2 V; I_{C} = -4 A; pulsed; t_{p} ≤ 300 μs; δ ≤ 0.02; T_{amb} = 25 °C	80	-	-	
		V_{CE} = -2 V; I_{C} = -6 A; pulsed; t_{p} ≤ 300 μs; δ ≤ 0.02; T_{amb} = 25 °C	30	-	-	
V _{CEsat}	collector-emitter saturation voltage	I _C = -0.5 A; I _B = -50 mA; T _{amb} = 25 °C	-	-46	-60	mV
		I _C = -1 A; I _B = -50 mA; T _{amb} = 25 °C	-	-70	-110	mV
		I _C = -2 A; I _B = -200 mA; T _{amb} = 25 °C	-	-120	-180	mV
		I_C = -4 A; I_B = -400 mA; pulsed; $t_p \le$ 300 μs; δ ≤ 0.02; T_{amb} = 25 °C	-	-220	-300	mV
		$I_C = -6 \text{ A}$; $I_B = -600 \text{ mA}$; pulsed; $t_p \le$	-	-320	-450	mV
R _{CEsat}	collector-emitter saturation resistance	300 μs; δ ≤ 0.02; T _{amb} = 25 °C	-	55	75	mΩ
V _{BEsat}	base-emitter saturation voltage	I _C = -0.5 A; I _B = -50 mA; T _{amb} = 25 °C	-	-0.8	-0.85	V
		I _C = -1 A; I _B = -50 mA; T _{amb} = 25 °C	-	-0.84	-0.9	V
		I_C = -1 A; I_B = -100 mA; pulsed; $t_p \le$ 300 μs; $δ \le 0.02$; T_{amb} = 25 °C	-	-0.84	-1	V
		I_C = -4 A; I_B = -400 mA; pulsed; $t_p \le$ 300 μs; δ ≤ 0.02; T_{amb} = 25 °C	-	-1	-1.1	V
V_{BEon}	base-emitter turn-on voltage	V _{CE} = -2 V; I _C = -2 A; T _{amb} = 25 °C	-	-0.8	-1	V
d	delay time	$V_{CC} = -10 \text{ V}; I_C = -2 \text{ A}; I_{Bon} = -0.1 \text{ A};$	-	12	-	ns
r	rise time	I _{Boff} = 0.1 A; T _{amb} = 25 °C	-	43	-	ns
on	turn-on time		-	55	=	ns
·s	storage time		-	240	-	ns
·f	fall time		-	80	=	ns
off	turn-off time		-	320	-	ns
ĪΤ	transition frequency	V _{CE} = -10 V; I _C = -0.1 A; f = 100 MHz; T _{amb} = 25 °C	-	110	-	MHz
C _c	collector capacitance	V _{CB} = -10 V; I _E = 0 A; i _e = 0 A; f = 1 MHz; T _{amb} = 25 °C	-	50	-	pF

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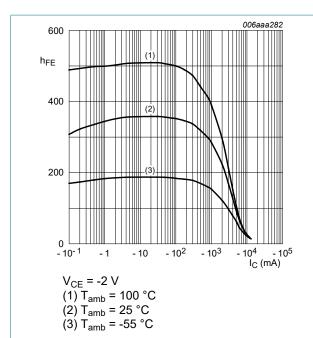


Fig. 5. DC current gain as a function of collector current; typical values

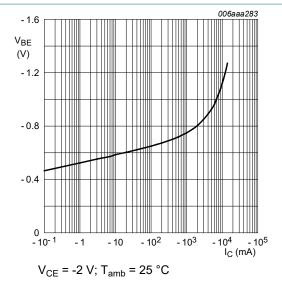


Fig. 6. Base-emitter voltage as a function of collector current; typical values

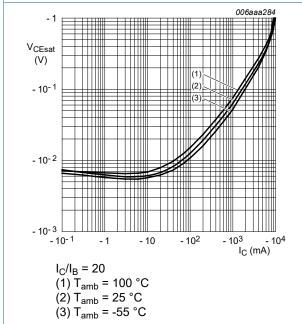


Fig. 7. Collector-emitter saturation voltage as a function of collector current; typical values

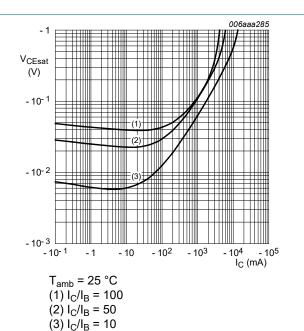


Fig. 8. Collector-emitter saturation voltage as a function of collector current; typical values

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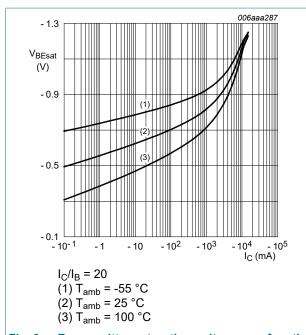


Fig. 9. collector current; typical values

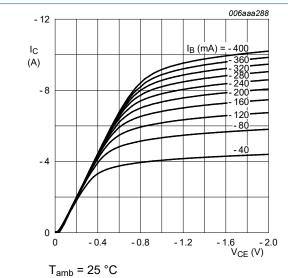
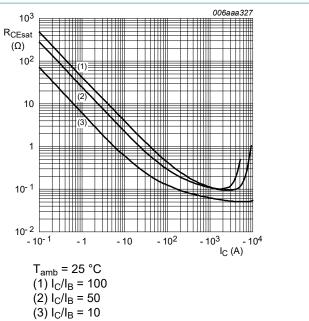
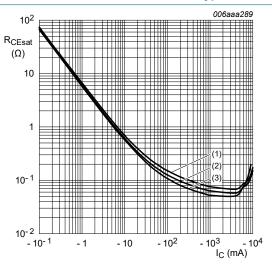


Fig. 11. Collector current as a function of collectoremitter voltage; typical values



Base-emitter saturation voltage as a function of Fig. 10. Collector-emitter saturation resistance as a function of collector current; typical values

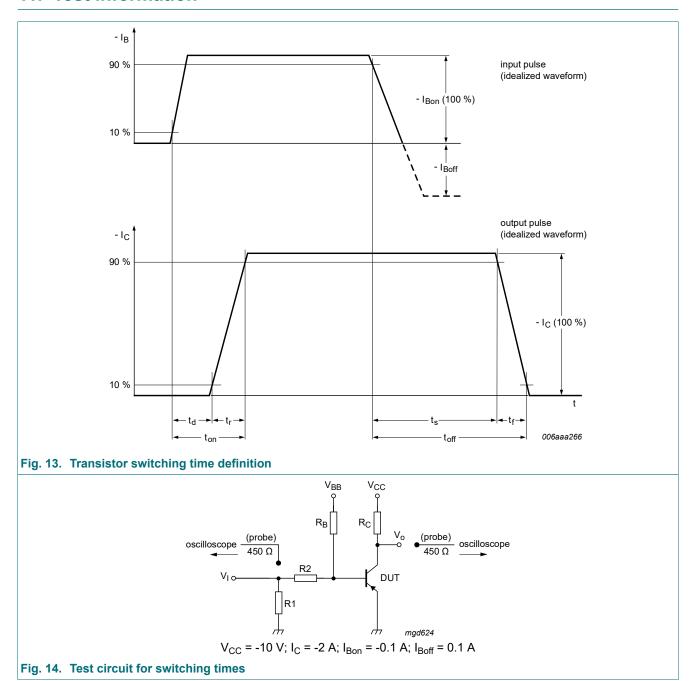


 $I_{\rm C}/I_{\rm B}=20$ (1) T_{amb} = 100 °C (2) $T_{amb} = 25 \, ^{\circ}C$ (3) $T_{amb} = -55 \, ^{\circ}C$

Fig. 12. Collector-emitter saturation resistance as a function of collector current; typical values

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11. Test information

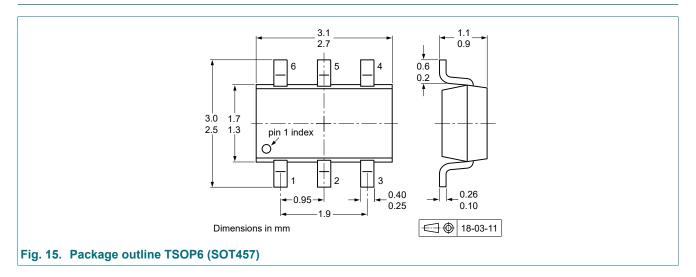


Quality information

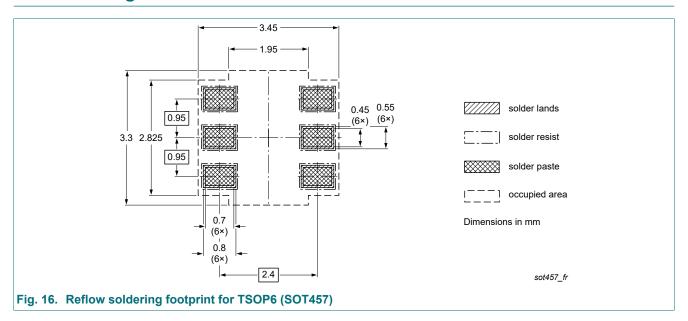
This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard *Q101 - Stress test qualification for discrete semiconductors*, and is suitable for use in automotive applications.

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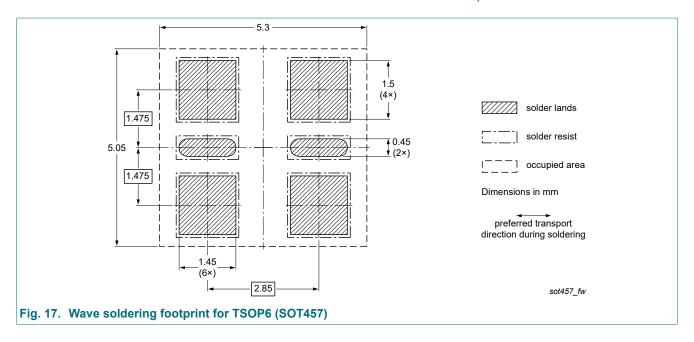
12. Package outline



13. Soldering



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14. Revision history

Table 8. Revision history

Table of Iteriorell inc.						
Data sheet ID	Release date	Data sheet status	Change notice	Supersedes		
PBSS5440D v.3	20230926	Product data sheet	-	PBSS5440D_2		
Modifications:	 The format of this data sheet has been redesigned to comply with the identity guidelines of Nexperia. Legal texts have been adapted to the new company name where appropriate. 					
PBSS5440D_2	20091214	Product data sheet	-	PBSS5440D_1		
PBSS5440D_1	20050427	Product data sheet	-	-		

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15. Legal information

Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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- [2] The term 'short data sheet' is explained in section "Definitions".
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